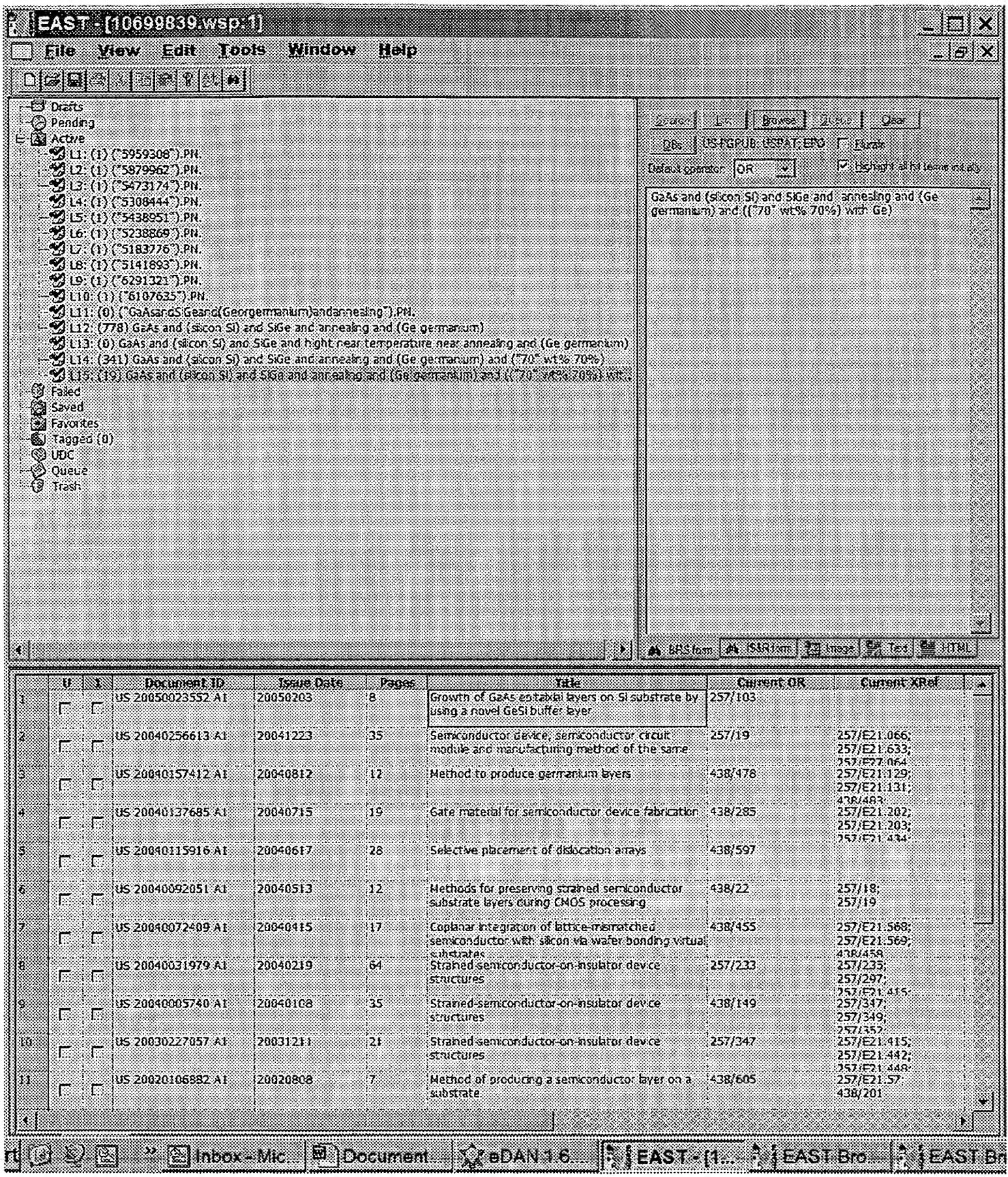

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	☐	☐	US 20050023552 A1	20050203	8	Growth of GaAs epitaxial layers on Si substrate by using a novel GeSi buffer layer	257/103	
2	☐	☐	US 20040256613 A1	20041223	35	Semiconductor device, semiconductor circuit module and manufacturing method of the same	257/19	257/E21.066; 257/E21.633; 257/E27.064
3	☐	☐	US 20040157412 A1	20040812	12	Method to produce germanium layers	438/478	257/E21.129; 257/E21.131; 438/483
4	☐	☐	US 20040137685 A1	20040715	19	Gate material for semiconductor device fabrication	438/285	257/E21.202; 257/E21.203; 257/E21.434
5	☐	☐	US 20040115916 A1	20040617	28	Selective placement of dislocation arrays	438/597	
6	☐	☐	US 20040092051 A1	20040513	12	Methods for preserving strained semiconductor substrate layers during CMOS processing	438/22	257/18; 257/19
7	☐	☐	US 20040072409 A1	20040415	17	Coplanar integration of lattice-mismatched semiconductor with silicon via wafer bonding virtual substrates	438/455	257/E21.568; 257/E21.569; 438/458
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9	☐	☐	US 20040005740 A1	20040108	35	Strained-semiconductor-on-insulator device structures	438/149	257/347; 257/349; 257/352
10	☐	☐	US 20030227057 A1	20031211	21	Strained semiconductor-on-insulator device structures	257/347	257/E21.415; 257/E21.442; 257/E21.448
11	☐	☐	US 20020106882 A1	20020808	7	Method of producing a semiconductor layer on a substrate	438/605	257/E21.57; 438/201

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